



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

BF420
BF422

TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.83 W ($T_{amb}=25^{\circ}C$)

Collector current

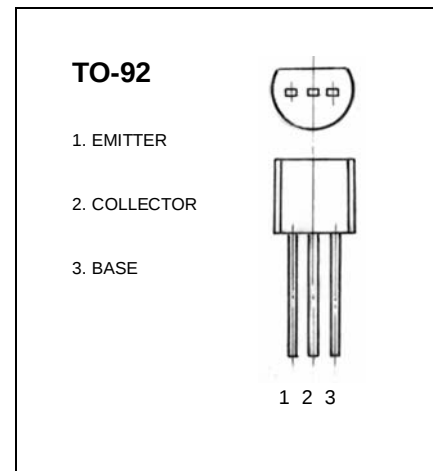
I_{CM} : 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: BF420 300 V
BF422 250 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage BF420 BF422	V_{CBO}	$I_C=100\mu A, I_E=0$	300 250		V
Collector-emitter breakdown voltage BF420 BF422	V_{CEO}	$I_C=1mA, I_B=0$	300 250		V
Emitter-base breakdown voltage	V_{EBO}	$I_E=100\mu A, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=200V, I_E=0$		0.01	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$		0.05	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=20V, I_C=25mA$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=30mA, I_B=5mA$		0.6	V
Transition frequency	f_T	$V_{CE}=10V, I_C=10mA$ $f=100MHz$	60		MHz